

Enhancement Mode N-Channel Power MOSFET

Features

- ◆ Low $R_{DS(on)}$ & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

Applications

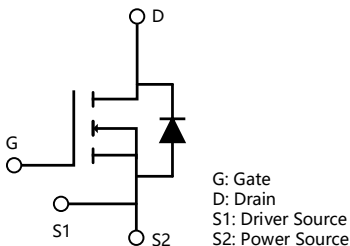
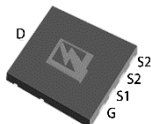
- ◆ Lighting
- ◆ Hard switching PWM
- ◆ Server power supply
- ◆ Charger

■ General Description

OSG65R200JF uses advanced GreenMOS™ technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for active power factor correction and switching mode power supply applications.

◆ $V_{DS, min@Tjmax}$	700 V
◆ $I_{D, pulse}$	60 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	200 mΩ
◆ Q_g	24.8 nC

■ Schematic and Package Information

SCHEMATIC DIAGRAM	PIN ASSIGNMENT-TOP VIEW
 <p>G: Gate D: Drain S1: Driver Source S2: Power Source</p>	 <p>PDFN8×8 OSG65R200JF</p>

■ Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	650	V
Gate source voltage	V_{GS}	±30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	20	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		12.5	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	60	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	151	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	600	mJ
Single pulsed avalanche current ⁵⁾	I_{AS}	10.9	A
Repetitive avalanche energy	E_{AR}	0.8	mJ
Repetitive avalanche current	I_{AR}	10.9	A
MOSFET dv/dt ruggedness, $V_{DS}=0\text{...}480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS}=0\text{...}480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.82	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$

■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
		700	774			$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}, T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.16	0.2	Ω	$V_{GS}=10\text{ V}, I_D=10\text{ A}$
			0.42			$V_{GS}=10\text{ V}, I_D=10\text{ A}, T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V}$

■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1433		pF	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V}, f=1\text{ MHz}$
Output capacitance	C_{oss}		925		pF	
Reverse transfer capacitance	C_{rss}		3.9		pF	
Turn-on delay time	$t_{d(on)}$		40.1		ns	$V_{GS}=10\text{ V}, V_{DS}=520\text{ V}, R_G=25\ \Omega, I_D=20\text{ A}$
Rise time	t_r		49.8		ns	
Turn-off delay time	$t_{d(off)}$		57.3		ns	
Fall time	t_f		63.7		ns	

■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		24.8		nC	$I_D=20\text{ A}$, $V_{DS}=520\text{ V}$, $V_{GS}=10\text{ V}$
Gate-source charge	Q_{gs}		7.2		nC	
Gate-drain charge	Q_{gd}		8.2		nC	
Gate plateau voltage	V_{plateau}		5.6		V	

■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	I_S			20	A	$V_{GS} < V_{th}$
Pulsed source current	I_{SP}			60		
Diode forward voltage	V_{SD}			1.4	V	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		380		ns	$V_R=400\text{ V}$, $I_S=20\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		5.3		μC	
Peak reverse recovery current	I_{rrm}		25.7		A	

■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=150\text{ V}$, $R_G=25\text{ }\Omega$, $L=10.8\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

■ **Electrical Characteristics Diagrams**

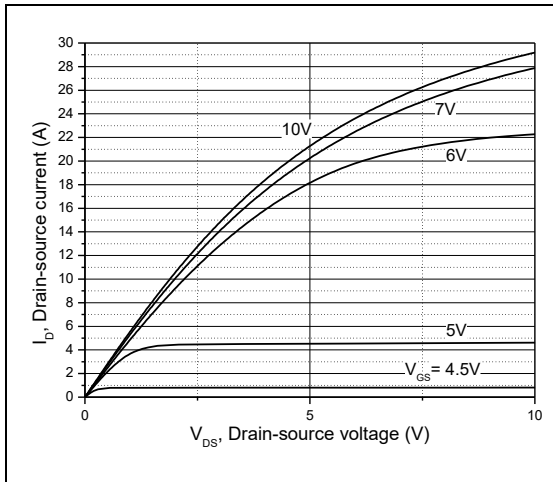


Figure 1, Typ. output characteristics

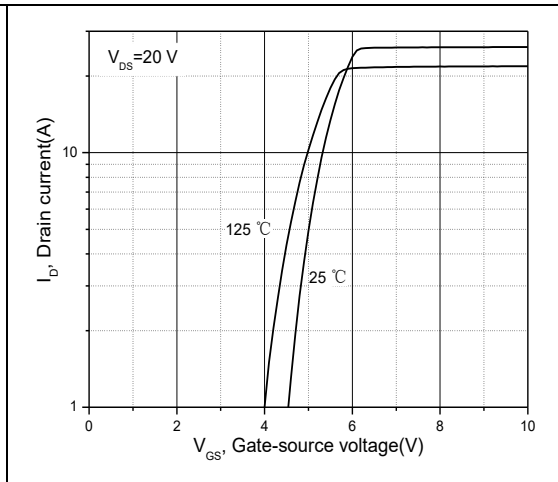


Figure 2, Typ. transfer characteristics

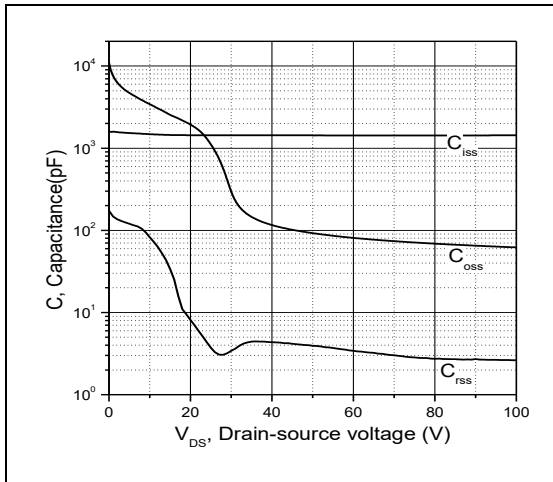


Figure 3, Typ. capacitances

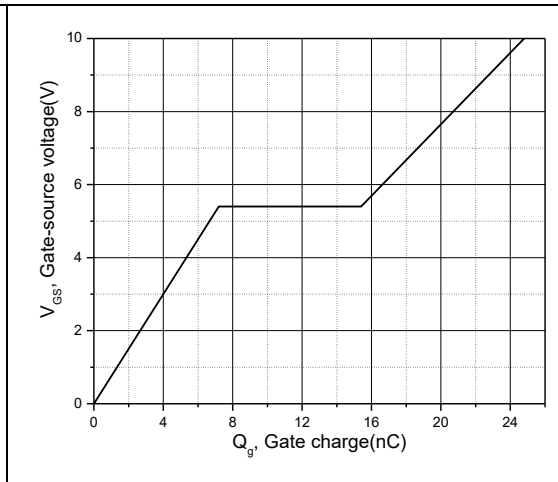


Figure 4, Typ. gate charge

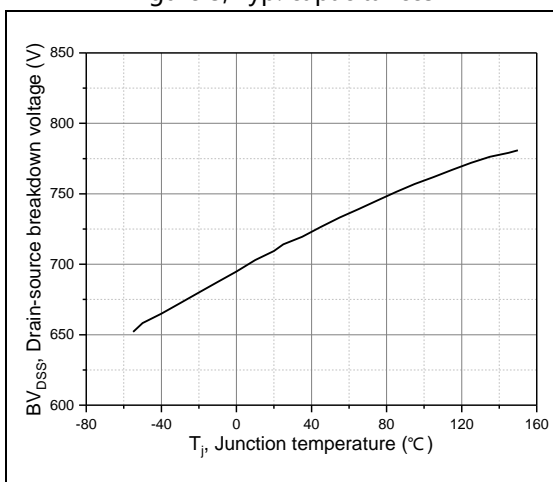


Figure 5, Drain-source breakdown voltage

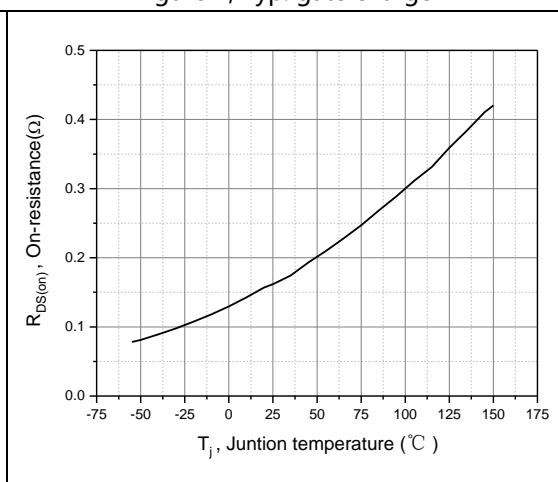


Figure 6, Drain-source on-state resistance

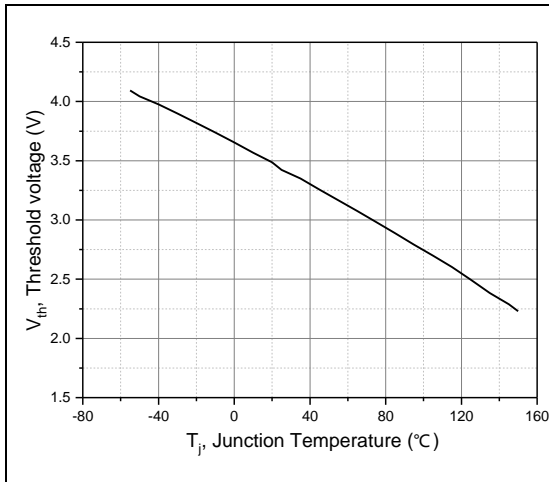


Figure 7, Threshold voltage

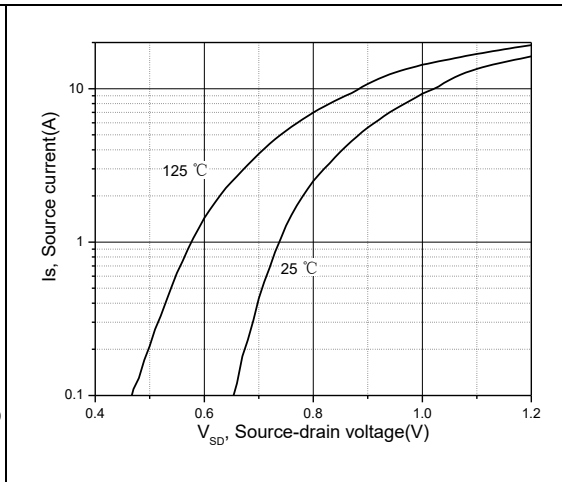


Figure 8, Forward characteristic of body diode

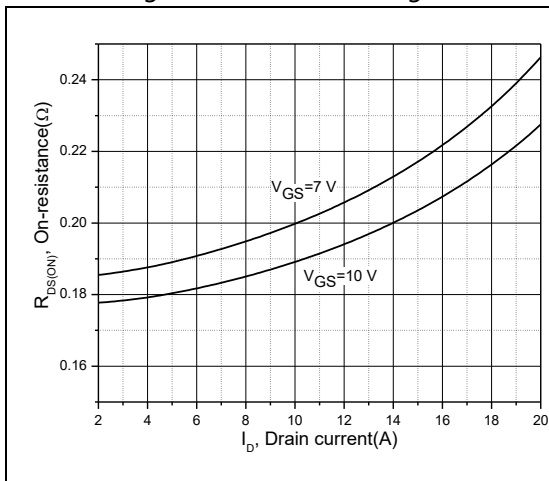


Figure 9, Drain-source on-state resistance

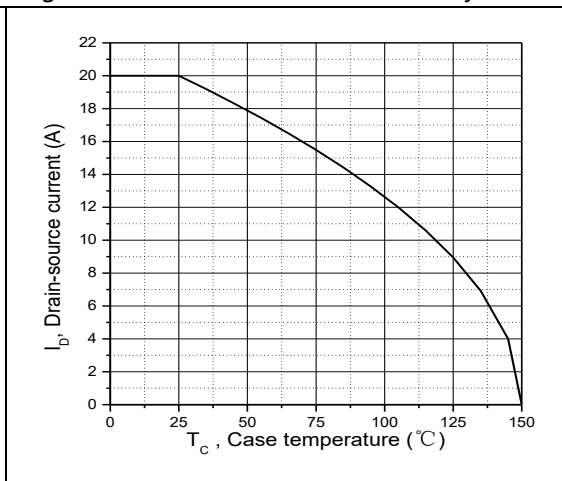


Figure 10, Drain current

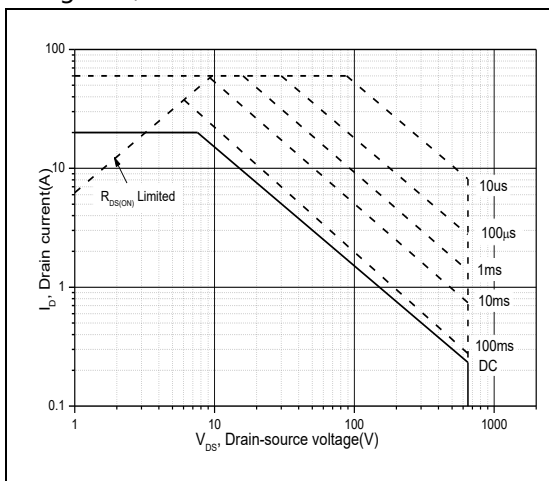


Figure 11, Safe operation area $T_C=25\text{ }^\circ\text{C}$

■ Test circuits and waveforms

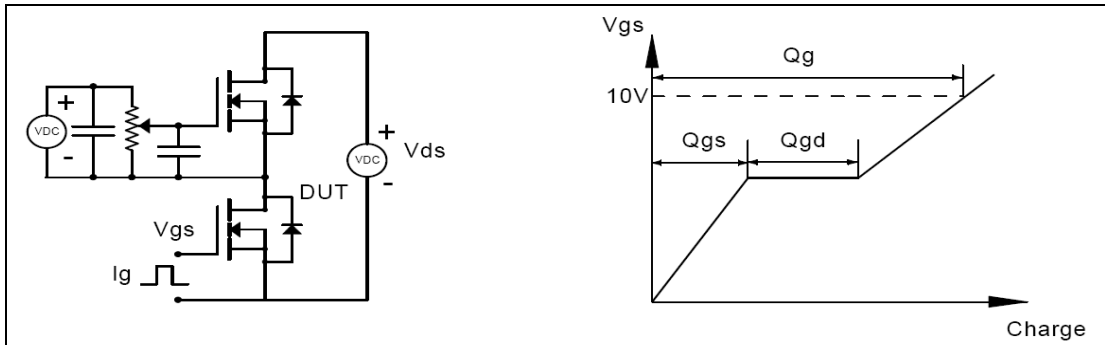


Figure 1, Gate charge test circuit & waveform

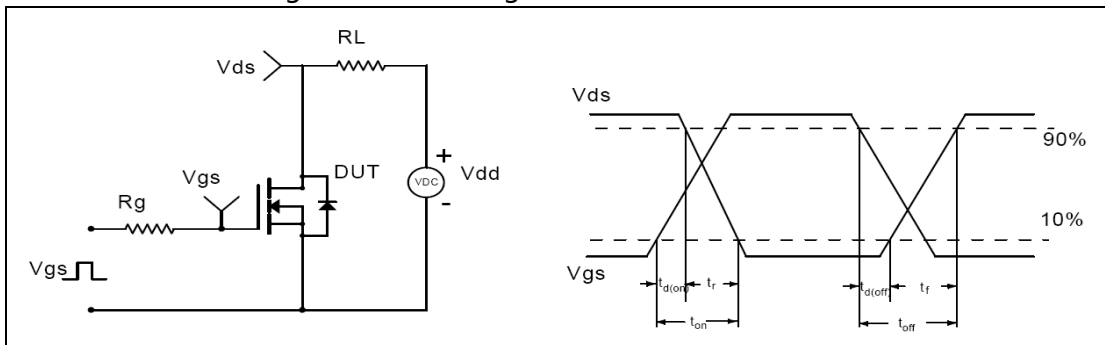


Figure 2, Switching time test circuit & waveforms

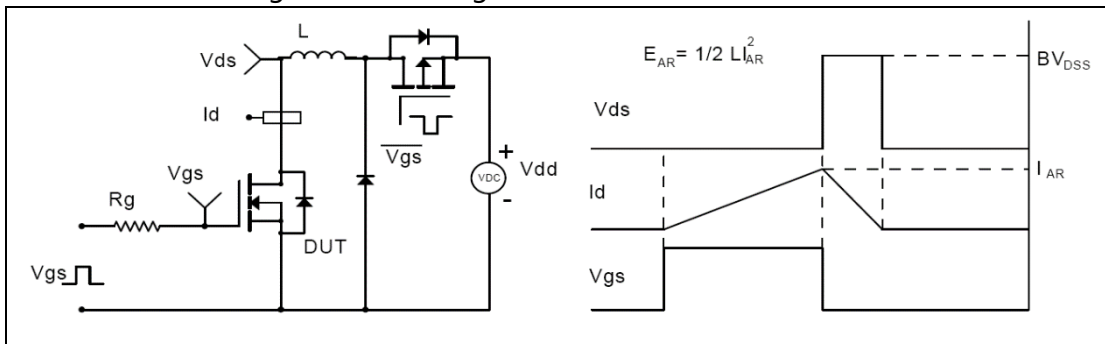


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

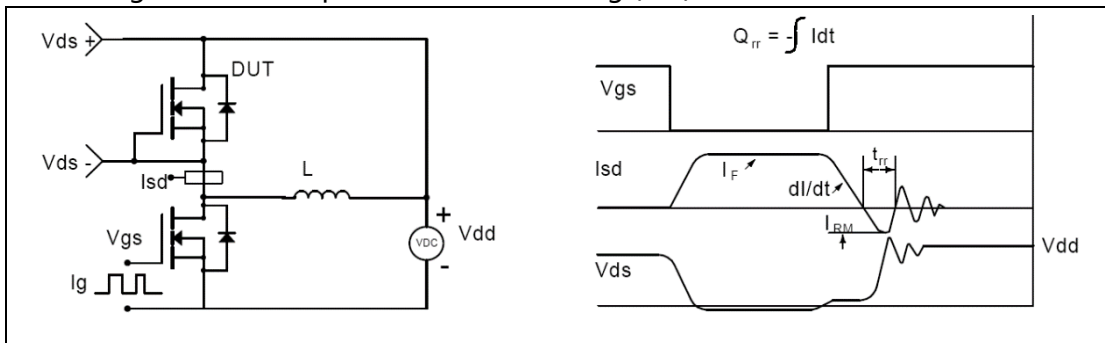
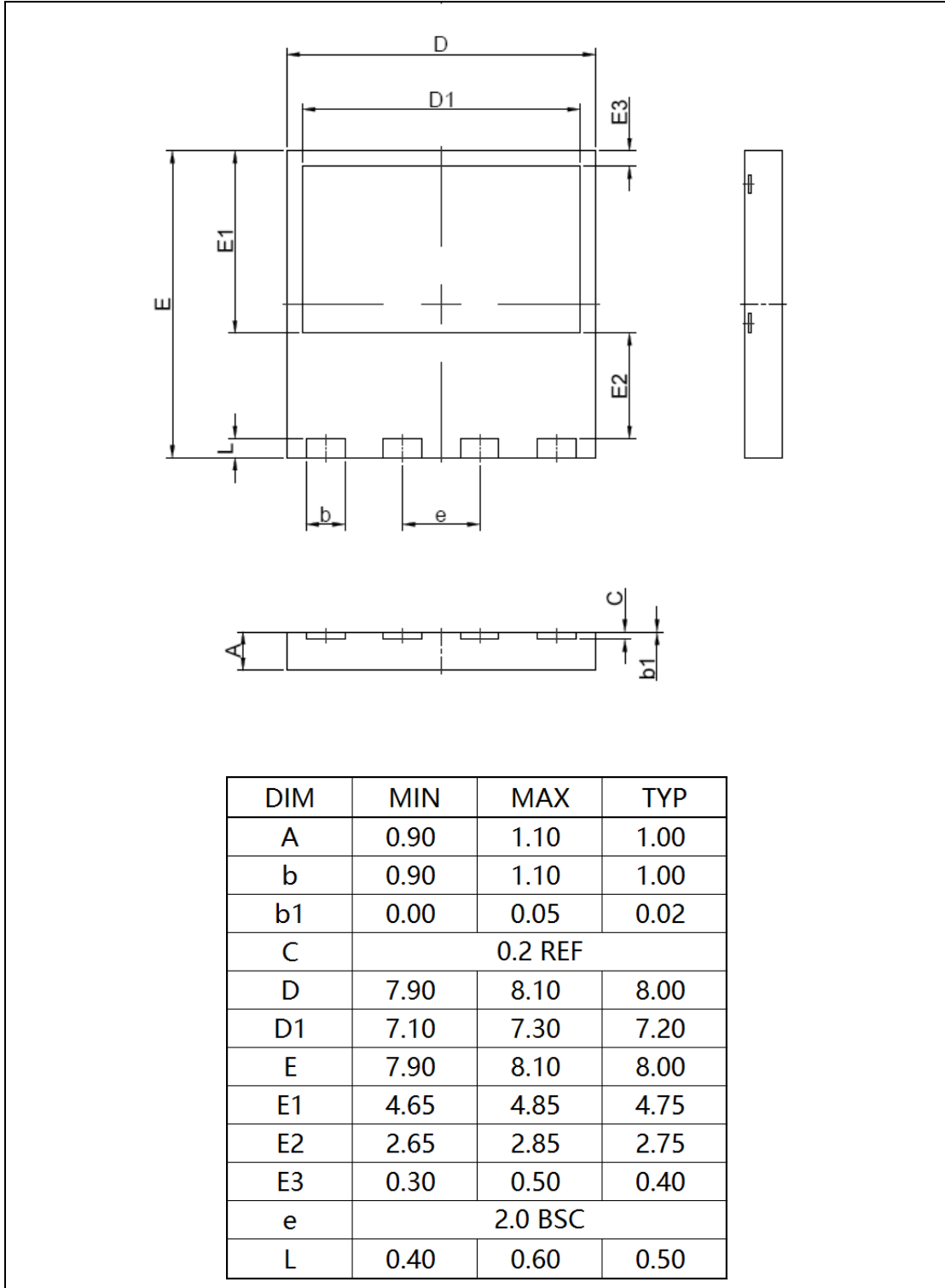


Figure 4, Diode reverse recovery test circuit & waveforms

■ **Package Information**

Figure1, PDFN8×8 package outline dimension



■ Ordering Information

Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
PDFN8×8	2500	2	5000	5	25000

■ Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R200JF	PDFN8×8	yes	yes	yes